

# **SMP75-8**

# TRISIL<sup>™</sup> FOR TELECOM EQUIPMENT PROTECTION

#### FEATURES

- Bidirectional crowbar protection
- Voltage: 8V
- Low leakage current : I<sub>R</sub> = 2µA max
- Holding current: I<sub>H</sub> = 150 mA min
- Repetitive peak pulse current : IPP = 75 A (10/1000µs)

#### MAIN APPLICATIONS

Any sensitive equipment requiring protection against lightning strikes and power crossing:

■ Ethernet, T1/E1

### DESCRIPTION

The SMP75-8 is a very low voltage transient surge arrestor especially designed to protect sensitive telecommunication equipment against lightning strikes and other transients. Its low voltage makes it suitable to protect low voltage transformer in T1/ E1, ethernet links without saturation of the transformer.

### BENEFITS

Trisils are not subject to ageing and provide a fail safe mode in short circuit for a better protection. They are used to help equipment to meet main standards such as UL1950, IEC950 / CSA C22.2 and UL1459. They have UL94 V0 approved resin. SMB package is JEDEC registered (DO-214AA). Trisils comply with the following standards GR-1089 Core, ITU-T-K20/K21, VDE0433, VDE0878, IEC61000-4-5 and FCC part 68.



#### Table 1: Order Code

Part Number	Marking	
SMP75-8	L08	

### Figure 1: Schematic Diagram



TM: TRISIL is a trademark of STMicroelectronics.

# SMP75-8

STANDARD	Peak Surge Voltage (V)	Waveform Voltage	Required peak current (A)	Current waveform	Minimum serial resistor to meet standard (Ω)
GR-1089 Core First level	2500 1000	2/10 μs 10/1000 μs	500 100	2/10 μs 10/1000 μs	5 3.3
GR-1089 Core Second level	5000	2/10 µs	500	2/10 µs	10
GR-1089 Core Intra-building	1500	2/10 µs	100	2/10 µs	0
ITU-T-K20/K21	6000 1500	10/700 µs	150 37.5	5/310 µs	10 0
ITU-T-K20 (IEC61000-4-2)	8000 15000	1/60 ns	ESD contact discharge ESD air discharge		0 0
VDE0433	4000 2000	10/700 µs	100 5/310 μs		0 0
VDE0878	4000 2000	1.2/50 µs	100 50	1/20 µs	0 0
IEC61000-4-5	4000 4000	10/700 μs 1.2/50 μs	100 100	5/310 μs 8/20 μs	0 0
FCC Part 68, lightning surge type A	1500 800	10/160 μs 10/560 μs	200 100	10/160 μs 10/560 μs	2.5 0
FCC Part 68, lightning surge type B	1000	9/720 µs 25 5/320 µs		0	

# Table 2: In compliances with the following standards

# Table 3: Absolute Ratings $(T_{amb} = 25^{\circ}C)$

Symbol	Parameter	Value	Unit	
Ірр	Repetitive peak pulse current	10/1000 μs 8/20 μs 10/560 μs 5/310 μs 10/160 μs 1/20 μs 2/10 μs	75 250 100 120 150 250 250	A
I <sub>FS</sub>	Fail-safe mode : maximum current (note 1)	5	kA	
I <sub>TSM</sub>	Non repetitive surge peak on-state current (sinusoidal)	t = 0.2 s t = 1 s t = 2 s t = 15 mn	14 8 6.5 2	A
l <sup>2</sup> t	I <sup>2</sup> t value for fusing	12 12.2	A <sup>2</sup> s	
T <sub>stg</sub> Tj	Storage temperature range Maximum junction temperature	-55 to 150 150	°C	
ΤL	Maximum lead temperature for soldering during 10 s.		260	°C

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Note 1: in fail safe mode, the device acts as a short circuit

#### **Table 4: Thermal Resistances**

Symbol	Parameter	Value	Unit
R <sub>th(j-a)</sub>	Junction to ambient (with recommended footprint)	100	°C/W
R <sub>th(j-l)</sub>	Junction to leads	20	°C/W

# Table 5: Electrical Characteristics (T<sub>amb</sub> = 25°C)

Symbol	Parameter
V <sub>RM</sub>	Stand-off voltage
V <sub>BR</sub>	Breakdown voltage
V <sub>BO</sub>	Breakover voltage
I <sub>RM</sub>	Leakage current
IPP	Peak pulse current
I <sub>BO</sub>	Breakover current
IH	Holding current
VR	Continuous reverse voltage
I <sub>R</sub>	Leakage current at V <sub>R</sub>
С	Capacitance



	I <sub>RM</sub> @	♀ V <sub>RM</sub>	I <sub>R</sub> @	V <sub>R</sub>	Dynamic V <sub>BO</sub>		atic @ I <sub>BO</sub>	I <sub>H</sub>	С
Types	m	NV.	max.		max.	max.	max.	typ.	max.
	max.	no	te1	note 2	not	e 3	note 4	note 5	
	μA	V	μA	V	V	V	mA	mA	pF
SMP75-8	2	6	5	8	20	15	800	50	60

Note 1: IR measured at VR guarantee VBR min  $\geq$  VR

Note 2: see functional test circuit 1

Note 3: see test circuit 2

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Note 4: see functional holding current test circuit 3

Note 5:  $V_R = 2V$  bias,  $V_{RMS} = 1V$ , F = 1MHz

### Figure 2: Pulse waveform



# Figure 3: Non repetitive surge peak on-state current versus overload duration



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# Figure 4: On-state voltage versus on-state current (typical values)







Figure 8: Variation of thermal impedance junction to ambient versus pulse duration (Printed circuit board FR4, SCu=35µm, recommended pad layout)



# Figure 5: Relative variation of holding current versus junction temperature



Figure 7: Relative variation of leakage current versus reverse voltage applied (typical values)



Figure 9: Relative variation of junction capacitance versus reverse voltage applied (typical values)



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# Figure 10: Test circuit 1 for dynamic $I_{BO}$ and $V_{BO}$ parameters















		DIMEN	ISIONS	
REF.	Millin	neters	Inc	hes
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.075	0.096
A2	0.05	0.20	0.002	0.008
b	1.95	2.20	0.077	0.087
С	0.15	0.41	0.006	0.016
Е	5.10	5.60	0.201	0.220
E1	4.05	4.60	0.159	0.181
D	3.30	3.95	0.130	0.156
L	0.75	1.60	0.030	0.063

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### Figure 14: Foot Print Dimensions (in millimeters)



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

# **Table 6: Ordering Information**

Part Number	Marking	Package	Weight	Base qty	Delivery mode
SMP75-8	L08	SMB	0.11 g	2500	Tape & reel

### **Table 7: Revision History**

Date	Revision	Description of Changes
19-July-2005	3	Previous issue
02-Jan-2006	4	Added ECOPACK statement and changed page layout. Minor updates to technical values in Tables 2, 3, and 5.

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